NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI HF75-50F** is 50 V Class AB NPN Power transistor, designed for SSB & VHF Communacations.

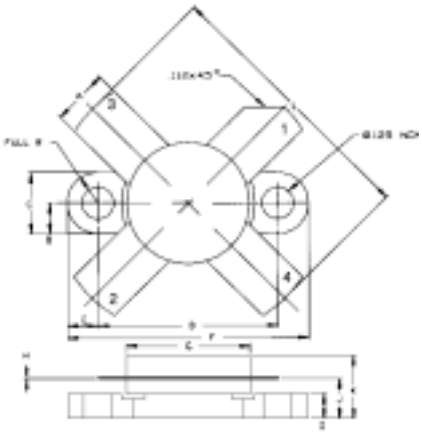
FEATURES:

- P_G = 14 dB min. at 75 W/30 MHz
- IMD_3 = 50 dBc max. at 75 W(PEP)
- ***Omnigold***™ Metalization System
- 50 V Operation

MAXIMUM RATINGS

I_C	3.25 A
V_{CBO}	110 V
V_{CEO}	55 V
V_{EBO}	4.0 V
P_{DISS}	127 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.0 °C/W

PACKAGE STYLE .500 4L FLG



1 = COLLECTOR 2 = BASE
3 & 4 EMITTER

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.125/3,18	
C	.245/6,22	.255/6,48
D	.720/18,28	.730/18,54
E	.125/3,18	
F	.970/24,64	.980/24,89
G	.495/12.57	.505/12.83
H	.003/0,08	.007/0,18
I	.090/2,29	.110/2,79
J	.160/4,06	.175/4,45
K		.280/7,11
L		1.050/26,67

ORDER CODE: ASI10610

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 100 mA	110			V
BV_{CE0}	I_C = 200 mA	55			V
BV_{EBO}	I_E = 10 mA	4.0			V
h_{FE}	V_{CE} = 6.0 V I_C = 1.4 A	19	---	50	---
C_{ob}	V_{CB} = 50 V f = 1.0 MHz			100	pF
G_P IMD_3 η_C	V_{CE} = 50 V P_{IN} = 3.0 W P_{OUT} = 75 W(PEP) f_1 = 30.000 MHz, f_2 = 30.001 MHz	14 --- 37	---	-30	dB dBc %

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Specifications are subject to change without notice.